

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI TVU100** is Designed for

**FEATURES:**

- Input Matching Network
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	10 A
<b>V<sub>CB</sub></b>	60 V
<b>V<sub>CE</sub></b>	35 V
<b>P<sub>DISS</sub></b>	140 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	1.0 °C/W

**PACKAGE STYLE .450 BAL FLG(A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.055 / 1.40
B	.120 / 3.05	.130 / 3.30
C		.785 / 19.94
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F		.230 / 5.84
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N		.195 / 4.95
P	.445 / 11.30	.455 / 11.56

**ORDER CODE: ASI10651**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	35			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 50 mA      R <sub>BE</sub> = 10 Ω	60			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>E</sub> = 28 V			5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	10		100	<b>---</b>
<b>P<sub>GE</sub></b>	V <sub>CE</sub> = 25 V      I <sub>CQ</sub> = 2 X 100 mA      f = 860 MHz P <sub>OUT</sub> = 100 W	8.5			<b>dB</b>